# Hilde H Hardtdegen

List of Publications by Year
in descending order

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| 235 | 3,187 | 147786 | 233409 |
|---|---|---|---|
| papers | citations | 31 h-index | 45 g-index |

| 244 | 244 | 244 | 3083 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | The Covalent Functionalization of Layered Black Phosphorus by Nucleophilic Reagents. Angewandte Chemie - International Edition, 2017, 56, 9891-9896. | 13.8 | 159 |
| 2 | The State of Strain in Single GaN Nanocolumns As Derived from Micro-Photoluminescence Measurements. Nano Letters, 2006, 6, 704-708. | 9.1 | 99 |
| 3 | Spin-orbit coupling and phase coherence in InAs nanowires. Physical Review B, 2010, 82, . | 3.2 | 79 |
| 4 | MOVPE growth of GaAs using a N2 carrier. Journal of Crystal Growth, 1992, 124, 420-426. | 1.5 | 70 |
| 5 | The Role of Si during the Growth of GaN Micro- and Nanorods. Crystal Growth and Design, 2014, 14, 1486-1492. | 3.0 | 70 |
| 6 | Suppression of weak antilocalization inGaxIn1â^'xAsâ^•InPnarrow quantum wires. Physical Review B, 2006, 74, . | 3.2 | 66 |
| 7 | Effect of Si-doping on InAs nanowire transport and morphology. Journal of Applied Physics, 2011, 110, . | 2.5 | 61 |
| 8 | Weak antilocalization in a polarization-doped AlxGa1â^'xNâ^•GaN heterostructure with single subband occupation. Applied Physics Letters, 2006, 88, 022111. | 3.3 | 52 |
| 9 | Weak antilocalization in gate-controlledAlxGa1â^'xNâ^•GaNtwo-dimensional electron gases. Physical Review B, 2006, 73, . | 3.2 | 51 |
| 10 | Modern chemical synthesis methods towards low-dimensional phase change structures in the Geâ€“Sbâ€“Te material system. Progress in Crystal Growth and Characterization of Materials, 2015, 61, 27-45. | 4.0 | 50 |
| 11 | Effect of carrier gas on GaN epilayer characteristics. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1408-1411. | 0.8 | 49 |
| 12 | Mechanism of mobility increase of the two-dimensional electron gas in AlGaNâ^•GaN heterostructures under small dose gamma irradiation. Journal of Applied Physics, 2008, 103, . | 2.5 | 46 |
| 13 | Alkalimanganselenide und -telluride A2Mn3X4 - Synthese, Kristall- und Spinstruktur. Zeitschrift Fur Anorganische Und Allgemeine Chemie, 1996, 622, 313-318. | 1.2 | 45 |
| 14 | Nanoimprint and selective-area MOVPE for growth of GaAs/InAs core/shell nanowires. Nanotechnology, 2013, 24, 085603. | 2.6 | 45 |
| 15 | A model structure for interfacial phase change memories: Epitaxial trigonal Ge1Sb2Te4. Journal of Alloys and Compounds, 2016, 679, 285-292. | 5.5 | 44 |
| 16 | Supercurrent in Nb/InAs-nanowire/Nb Josephson junctions. Journal of Applied Physics, 2012, 112, . | 2.5 | 43 |
| 17 | Realization of nanoscaled tubular conductors by means of GaAs/InAs core/shell nanowires. Nanotechnology, 2013, 24, 035203. | 2.6 | 43 |
| 18 | Demonstration of a current-controlled three-terminal Nbâ€“InxGa1â^'xAs/InP Josephson contact. Applied Physics Letters, 1998, 73, 2348-2350. | 3.3 | 42 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | Nano-LED array fabrication suitable for future single photon lithography. Nanotechnology, 2015, 26, 185302. | 2.6 | 41 |
| 20 | Optimization of modulationâ€doped Ga1â^'xInxAs/InP heterostructures towards extremely high mobilities. Journal of Applied Physics, 1993, 73, 4489-4493. | 2.5 | 40 |
| 21 | Weak antilocalization in high mobility <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">In</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:mi mathvariant="normal">As</mml:mi><mml:mo>â^•</mml:mo><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">P</mml:mi></mml:mrow></mml:math> | 3.2 | 38 |
| 22 | Direct electro-optical pumping for hybrid CdSe nanocrystal/III-nitride based nano-light-emitting diodes. Applied Physics Letters, 2016, 108, 061107. | 3.3 | 38 |
| 23 | MOVPE of n-doped GaAs and modulation doped GaAs/AlGaAs nanowires. Journal of Crystal Growth, 2010, 312, 635-640. | 1.5 | 37 |
| 24 | MOCVD of AlGaAs/GaAs with novel group III compounds. Journal of Electronic Materials, 1990, 19, 305-310. | 2.2 | 36 |
| 25 | Electrical behaviour of the based MSM-2DEG diode. Solid-State Electronics, 1997, 41, 25-31. | 1.4 | 36 |
| 26 | Influence of growth temperature on the selective area MOVPE of InAs nanowires on GaAs (111) B using N2 carrier gas. Journal of Crystal Growth, 2009, 311, 3813-3816. | 1.5 | 36 |
| 27 | Electrical Spin Injection into InN Semiconductor Nanowires. Nano Letters, 2012, 12, 4437-4443. | 9.1 | 36 |
| 28 | Magnetically and optically tunable terahertz radiation from Ta/NiFe/Pt spintronic nanolayers generated by femtosecond laser pulses. Applied Physics Letters, 2019, 114, . | 3.3 | 36 |
| 29 | Quantum confinement effect on the effective mass in two-dimensional electron gas of AlGaN/GaN heterostructures. Journal of Applied Physics, 2009, 105, . | 2.5 | 35 |
| 30 | Characterization of interface structure in GaInAs/InP superlattices by means of X-ray diffraction. Journal of Crystal Growth, 1992, 124, 583-588. | 1.5 | 34 |
| 31 | Enhanced spin-orbit scattering length in narrow <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">Al</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:mi mathvariant="normal">N</mml:mi><mml:mo>â^•</mml:mo><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math> | 3.2 | 34 |
| 32 | Modeling and experimental verification of deposition behavior during AlGaAs growth: a comparison for the carrier gases N2 and H2. Journal of Crystal Growth, 2001, 223, 21-28. | 1.5 | 33 |
| 33 | Internal strains and crystal structure of the layers in AlGaN/GaN heterostructures grown on a sapphire substrate. Journal of Applied Physics, 2009, 105, 063515. | 2.5 | 33 |
| 34 | In situ characterization of GaAs growth in nitrogen atmosphere during MOVPE: a comparison to hydrogen atmosphere. Journal of Crystal Growth, 1998, 195, 211-216. | 1.5 | 30 |
| 35 | Rashba effect in InGaAsâ^•InP parallel quantum wires. Applied Physics Letters, 2006, 88, 032102. | 3.3 | 30 |
| 36 | On the magnetic properties of Gd implanted GaN. Journal of Applied Physics, 2008, 103, 07D107. | 2.5 | 30 |

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| 37 | Manipulating InAs nanowires with submicrometer precision. Review of Scientific Instruments, 2011, 82, 113705. | 1.3 | 30 |
| 38 | Aharonov-Bohm effect in quasi-one-dimensionalIn0.77Ga0.23As/InP rings. Physical Review B, 1995, 51, 4336-4342. | 3.2 | 29 |
| 39 | Resolving ambiguities in nanowire field-effect transistor characterization. Nanoscale, 2015, 7, 18188-18197. | 5.6 | 29 |
| 40 | Barrier height enhancement of Schottky diodes onnâ€•In0.53Ga0.47As by cryogenic processing. Applied Physics Letters, 1993, 63, 1939-1941. | 3.3 | 28 |
| 41 | Josephson effect in Nb/two-dimensional electron gas structures using a pseudomorphic InxGa1â^'xAs/InP heterostructure. Applied Physics Letters, 1997, 71, 3575-3577. | 3.3 | 28 |
| 42 | Real-time calibration of wafer temperature, growth rate and composition by optical in-situ techniques during AlxGa1â^'xAs growth in MOVPE. Journal of Crystal Growth, 2002, 240, 87-97. | 1.5 | 28 |
| 43 | Efficient heat dissipation in AlGaN/GaN heterostructure grown on silver substrate. Applied Materials Today, 2017, 7, 134-137. | 4.3 | 28 |
| 44 | Andreev reflection and strongly enhanced magnetoresistance oscillations in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">In</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:mi mathvariant="normal">As</mml:mi><mml:mo>â•</mml:mo><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">P</mml:mi></mml:mrow></. Physical Review B, 20 | 3.2 | 26 |
| 45 | Fully photon operated transmistor / all-optical switch based on a layered Ge1Sb2Te4 phase change medium. FlatChem, 2020, 23, 100186. | 5.6 | 26 |
| 46 | Epitaxial growth and characterization of Fe thin films on wurtzite GaN(0001). Journal of Crystal Growth, 2005, 283, 500-507. | 1.5 | 24 |
| 47 | Crossover from Josephson Effect to Single Interface Andreev Reflection in Asymmetric Superconductor/Nanowire Junctions. Nano Letters, 2014, 14, 4977-4981. | 9.1 | 24 |
| 48 | Intra-atomic photoluminescence at 1.41 eV of substitutional Mn in GaMnN of high optical quality. Journal of Applied Physics, 2007, 101, 063504. | 2.5 | 23 |
| 49 | Nano-light-emitting-diodes based on InGaN mesoscopic structures for energy saving optoelectronics. Applied Physics Letters, 2016, 109, . | 3.3 | 23 |
| 50 | Novel organometallic starting materials for group IIIâ€“V semiconductor metal-organic chemical vapour deposition. Thin Solid Films, 1989, 174, 1-4. | 1.8 | 22 |
| 51 | Extremely high electron mobilities in modulation doped Ga1â^'xInxAs/InP heterostructures grown by LP-MOVPE. Journal of Crystal Growth, 1992, 116, 521-523. | 1.5 | 22 |
| 52 | Heavy carbon doping in low-pressure metalorganic vapor phase epitaxy of GaAs using trimethylarsenic â€” a comparison between the carrier gases N2 and H2. Journal of Crystal Growth, 1994, 145, 440-446. | 1.5 | 22 |
| 53 | InP/InGaAs photodetector based on a high electron mobility transistor layer structure: Its response at 1.3 Î¼m wavelength. Applied Physics Letters, 1995, 67, 106-108. | 3.3 | 19 |
| 54 | Gate-defined quantum-dot devices realized in InGaAs/InP by incorporating a HfO2 layer as gate dielectric. Applied Physics Letters, 2009, 94, 042114. | 3.3 | 18 |

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| 55 | Laser micro annealing conditioning for the suppression of statistical scatter in freestanding Sb2Te3 nanowire resistance. FlatChem, 2020, 21, 100164. | 5.6 | 18 |
| 56 | MOVPE growth and in situ characterization of GaN layers on sapphire substrates. Physica Status Solidi A, 2004, 201, 312-319. | 1.7 | 17 |
| 57 | Site-controlled growth of indium nitride based nanostructures using metalorganic vapour phase epitaxy. Journal of Crystal Growth, 2013, 370, 336-341. | 1.5 | 17 |
| 58 | Inhomogeneity of donor doping in SrTiO3 substrates studied by fluorescence-lifetime imaging microscopy. Applied Physics Letters, 2013, 103, . | 3.3 | 17 |
| 59 | Optical and structural properties of MOVPE grown GaxIn1â^'xAs/InP strained multiple quantum well atructures. Journal of Electronic Materials, 1992, 21, 293-298. | 2.2 | 16 |
| 60 | Novel HEMT layout: The RoundHEMT. Electronics Letters, 1995, 31, 589-591. | 1.0 | 16 |
| 61 | Femtosecond and highly sensitive GaAs metalâ€“semiconductorâ€“metal photodetectors grown on aluminum mirrors/pseudo-substrates. Semiconductor Science and Technology, 2010, 25, 075001. | 2.0 | 16 |
| 62 | Preparation of Ohmic contacts to GaAs/AlGaAs-core/shell-nanowires. Applied Physics Letters, 2012, 100, . | 3.3 | 16 |
| 63 | Conditioning nano-LEDs in arrays by laser-micro-annealing: The key to their performance improvement. Applied Physics Letters, 2021, 118, . | 3.3 | 16 |
| 64 | Coordinatively saturated Ga compounds â€" A new type of group III precursor for the MOCVD of GaAs. Journal of Crystal Growth, 1990, 102, 290-292. | 1.5 | 15 |
| 65 | Demonstration of the N2 carrier process for LP-MOVPE of. Journal of Crystal Growth, 1997, 170, 103-108. | 1.5 | 15 |
| 66 | MOVPE process for horizontal reactors with reduced parasitic deposition. Journal of Crystal Growth, 2004, 272, 407-414. | 1.5 | 15 |
| 67 | Mechanism of strain relaxation by twisted nanocolumns revealed in AlGaN/GaN heterostructures. Applied Physics Letters, 2009, 95, . | 3.3 | 15 |
| 68 | Long electron spin coherence in ion-implanted GaN: The role of localization. Applied Physics Letters, 2013, 102, . | 3.3 | 15 |
| 69 | Cutting-edge nano-LED technology. Journal of Applied Physics, 2022, 131, . | 2.5 | 15 |
| 70 | (AlGa)As grown by low pressure metalorganic vapor phase epitaxy using a N2 carrier. Journal of Electronic Materials, 1994, 23, 1061-1065. | 2.2 | 14 |
| 71 | Direct determination of the Andreev reflection probability by means of point contact spectroscopy. Applied Physics Letters, 2000, 76, 1152-1154. | 3.3 | 14 |
| 72 | On the influence of gas inlet configuration with respect to homogeneity in a horizontal single wafer MOVPE reactor. Journal of Crystal Growth, 2001, 223, 15-20. | 1.5 | 14 |

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| 73 | Zeeman splitting in ballistic GaInAsâˆ•InP split-gate quantum point contacts. Applied Physics Letters, 2007, 90, 122107. | 3.3 | 14 |
| 74 | Non-uniform distribution of induced strain in a gate-recessed AlGaN/GaN structure evaluated by micro-PL measurements. Semiconductor Science and Technology, 2012, 27, 105008. | 2.0 | 14 |
| 75 | Rashba effect in strained InGaAs/InP quantum wire structures. Science and Technology of Advanced Materials, 2003, 4, 19-25. | 6.1 | 13 |
| 76 | The growth mechanism of GaN with different H2/N2 carrier gas ratios. Journal of Crystal Growth, 2007, 307, 6-13. | 1.5 | 13 |
| 77 | Spinâ€“orbit coupling in Ga<sub>x</sub>In<sub>1â^'x</sub>As/InP two-dimensional electron gases and quantum wire structures. Semiconductor Science and Technology, 2009, 24, 064001. | 2.0 | 13 |
| 78 | Magnetic properties of Gdâ€doped GaN. Physica Status Solidi (B): Basic Research, 2014, 251, 1673-1684. | 1.5 | 13 |
| 79 | Metal organic vapor phase epitaxy of hexagonal Geâ€“Sbâ€“Te (GST). Journal of Crystal Growth, 2015, 420, 37-41. | 1.5 | 13 |
| 80 | Experimental determination of Rashba and Dresselhaus parameters andg<sup>*</sup>-factor anisotropy via Shubnikov-de Haas oscillations. New Journal of Physics, 2017, 19, 103012. | 2.9 | 13 |
| 81 | A new approach towards low-pressure metalorganic vapor phase epitaxy of (AlGa)As using triethylgallium and dimethylethylaminealane. Journal of Crystal Growth, 1994, 145, 478-484. | 1.5 | 12 |
| 82 | Spectral Sensitivity Tuning of Vertical InN Nanopyramid-Based Photodetectors. Japanese Journal of Applied Physics, 2013, 52, 08JF05. | 1.5 | 12 |
| 83 | MOVPE GaN growth: determination of activation energy using in-situ reflectometry. Journal of Crystal Growth, 2004, 272, 100-105. | 1.5 | 11 |
| 84 | Origin and limiting mechanism of induced nonequilibrium currents in gated two-dimensional electron systems. Physical Review B, 2009, 80, . | 3.2 | 11 |
| 85 | An outstanding innovation in LP-MOVPE: use of nitrogen as the carrier gas. III-Vs Review, 1995, 8, 34-39. | 0.0 | 10 |
| 86 | Nucleation of wavy growth modes in quantum well stacks of IIIâ€“V compound alloys. Journal of Crystal Growth, 1995, 152, 115-126. | 1.5 | 10 |
| 87 | Uniform III-nitride growth in single wafer horizontal MOVPE reactors. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 744-748. | 1.8 | 10 |
| 88 | Rashba effect in GaxIn1-xAs/InP quantum wire structures. Applied Physics A: Materials Science and Processing, 2007, 87, 577-584. | 2.3 | 10 |
| 89 | Low-temperature conductance of the weak junction in InAs nanowire in the field of AFM scanning gate. JETP Letters, 2011, 93, 10-14. | 1.4 | 10 |
| 90 | Magnetism in GaN layers implanted by La, Gd, Dy and Lu. Thin Solid Films, 2011, 519, 6120-6125. | 1.8 | 10 |

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| 91 | Frequency anomaly in the Rashba-effect induced magnetization oscillations of a high-mobility two-dimensional electron system. Physical Review B, 2013, 87, . | 3.2 | 10 |
| 92 | Evolution and characteristics of GaN nanowires produced via maskless reactive ion etching. Nanotechnology, 2014, 25, 255301. | 2.6 | 10 |
| 93 | New Group III Precursors for the Movpe of GaAs and InP Based Material. Materials Research Society Symposia Proceedings, 1989, 145, 205. | 0.1 | 9 |
| 94 | Suppression of wavy growth in metalorganic vapor phase epitaxy grown GaInAs/InP superlattices. Applied Physics Letters, 1996, 69, 2101-2103. | 3.3 | 9 |
| 95 | Deep-level states in MOVPE AlGaAs:. Journal of Crystal Growth, 1998, 186, 13-20. | 1.5 | 9 |
| 96 | Adjustment of the critical current in a Nbâ€“InxGa1â^'xAs/InP Josephson contact by light exposure. Applied Physics Letters, 1999, 75, 391-393. | 3.3 | 9 |
| 97 | On the choice of precursors for the MOVPE-growth of high-quality Al0.30Ga0.70As/GaAs v-groove quantum wires with large subband spacing. Journal of Crystal Growth, 2000, 221, 91-97. | 1.5 | 9 |
| 98 | Electron transport in modulation-doped GaAs v-groove quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 760-765. | 2.7 | 9 |
| 99 | Use of SiC band gap temperature dependence for absolute calibration of emissivity corrected pyrometers in III-nitride MOVPE. Journal of Crystal Growth, 2004, 272, 81-86. | 1.5 | 9 |
| 100 | Influence of growth temperature on GaN:Cr incorporation and structural properties in MOVPE. Journal of Crystal Growth, 2009, 312, 1-9. | 1.5 | 9 |
| 101 | Vertically integrated (Ga, In)N nanostructures for future single photon emitters operating in the telecommunication wavelength range. Nanotechnology, 2013, 24, 405302. | 2.6 | 9 |
| 102 | Electronic edge-state and space-charge phenomena in long GaN nanowires and nanoribbons. Nanotechnology, 2017, 28, 135204. | 2.6 | 9 |
| 103 | Nano-LED induced chemical reactions for structuring processes. Nanoscale Advances, 2020, 2, 5421-5427. | 4.6 | 9 |
| 104 | AlGaN/GaN Round-HEMTs on (111) silicon substrates. Electronics Letters, 2001, 37, 1364. | 1.0 | 9 |
| 105 | Electrical and structural studies of AlGaAs/GaAs wires grown on patterned substrates. Applied Surface Science, 1998, 123-124, 687-693. | 6.1 | 8 |
| 106 | Electron states, magneto-transport and carrier dynamics in modulation-dopedV-groove quantum wires. Solid-State Electronics, 1998, 42, 1245-1249. | 1.4 | 8 |
| 107 | Use of wafer temperature determination for the study of unintentional parameter influences for the MOVPE of III-nitrides. Physica Status Solidi (B): Basic Research, 2005, 242, 2581-2586. | 1.5 | 8 |
| 108 | g-factor and exchange energy in a few-electron lateral InGaAs quantum dot. Applied Physics Letters, 2009, 95, . | 3.3 | 8 |

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| 109 | Comparison of InAs nanowire conductivity: influence of growth method and structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 230-234. | 0.8 | 8 |
| 110 | The electronic transport of top subband and disordered sea in an InAs nanowire in the presence of a mobile gate. Journal of Physics Condensed Matter, 2014, 26, 165304. | 1.8 | 8 |
| 111 | Impact of thermal annealing on nonequilibrium carrier dynamics in single-crystal, freestanding GaAs mesostructures. Semiconductor Science and Technology, 2014, 29, 045022. | 2.0 | 8 |
| 112 | Polymorphous GdScO 3 as high permittivity dielectric. Journal of Alloys and Compounds, 2015, 651, 514-520. | 5.5 | 8 |
| 113 | Compact extreme ultraviolet source for laboratory-based photoemission spectromicroscopy. Applied Physics Letters, 2016, 108, . | 3.3 | 8 |
| 114 | Electrical and optical characterization of freestanding Ge<inf>1</inf>Sb<inf>2</inf>Te<inf>4</inf> nano-membranes integrated in coplanar strip lines. , 2016, , . | | 8 |
| 115 | Characterization of hydrogen passivation and carbon self-compensation of highly C-doped GaAs by means of x-ray diffraction. Journal of Applied Physics, 1996, 79, 710. | 2.5 | 7 |
| 116 | Suppression of weak antilocalization in anAlxGa1âˆ’xNâˆ•GaNtwo-dimensional electron gas by an in-plane magnetic field. Physical Review B, 2007, 75, . | 3.2 | 7 |
| 117 | Influence of the reactor inlet configuration on the AlGaN growth efficiency. Journal of Crystal Growth, 2007, 298, 413-417. | 1.5 | 7 |
| 118 | Investigations of local electronic transport in InAs nanowires by scanning gate microscopy at liquid helium temperatures. JETP Letters, 2014, 100, 32-38. | 1.4 | 7 |
| 119 | Quantum dots in InAs nanowires induced by surface potential fluctuations. Nanotechnology, 2014, 25, 135203. | 2.6 | 7 |
| 120 | High-field quasi-ballistic transport in AlGaN/GaN heterostructures. Applied Physics Letters, 2014, 104, 072105. | 3.3 | 7 |
| 121 | Growth of modulation-doped quantum wires on V-groove patterned substrates. Journal of Crystal Growth, 1997, 170, 605-610. | 1.5 | 6 |
| 122 | Observation of quantized conductance in split-gate In0.53Ga0.47As/In0.77Ga0.23As/InP point contacts using Cr/Au p-InP Schottky barriers. Journal of Applied Physics, 1998, 83, 2360-2362. | 2.5 | 6 |
| 123 | Shot noise of large charge quanta in superconductor/semiconductor/superconductor junctions. Physical Review B, 2005, 71, . | 3.2 | 6 |
| 124 | Study on growth and electrical performance of doubleâ€heterostructure AlGaN/GaN/AlGaN fieldâ€effectâ€transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1003. | 0.8 | 6 |
| 125 | Selfâ€assembled GaN nanostructures by dry etching and their optical properties. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 443-446. | 1.8 | 6 |
| 126 | Residual strain in recessed AlGaN/GaN heterostructure fieldâ€effect transistors evaluated by micro photoluminescence measurements. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 911-914. | 0.8 | 6 |

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| 127 | Distortions of the coulomb blockade conductance line in scanning gate measurements of inas nanowire based quantum dots. Journal of Experimental and Theoretical Physics, 2013, 116, 138-144. | 0.9 | 6 |
| 128 | Highly Transparent Conducting Polymer Top Contacts for Future IIIâ€“Nitride Based Single Photon Emitters. Japanese Journal of Applied Physics, 2013, 52, 08JH10. | 1.5 | 6 |
| 129 | Hybrid optoelectronics based on a nanocrystal/III-N nano-LED platform. , 2016, , . | | 6 |
| 130 | Generation of terahertz transients from <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Co</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:mi>Cr</mml:mi><mml:mi>Al</mml:mi></mml:mrow></mml:math>-Heusler-alloy/normal-metal nanobilayers excited by femtosecond optical pulses. Physical Review Research, 2021, 3, . | 3.6 | 6 |
| 131 | Epitaxial gallium arsenide for nuclear radiation detector applications. Nuclear Physics, Section B, Proceedings Supplements, 1995, 44, 381-385. | 0.4 | 5 |
| 132 | MOMBE and characterization of InAs and (Al,Ga)Sb. Journal of Crystal Growth, 1998, 188, 32-38. | 1.5 | 5 |
| 133 | Optoelectronic d.c. and r.f. behavior ofInP/InGaAs based HEMTs. Solid-State Electronics, 1998, 42, 197-200. | 1.4 | 5 |
| 134 | In-situ doping and implantation of GaN layers with Mn. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S646-S649. | 0.8 | 5 |
| 135 | Strain-enhanced electron mobility anisotropy in InxGa1â^'xAs/InP two-dimensional electron gases. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1130-1133. | 2.7 | 5 |
| 136 | LaLuO<sub>3</sub>as a high-kgate dielectric for InAs nanowire structures. Semiconductor Science and Technology, 2010, 25, 085001. | 2.0 | 5 |
| 137 | New method of creation of a rearrangeable local Coulomb potential profile and its application for investigations of local conductivity of InAs nanowires. Physica E: Low-Dimensional Systems and Nanostructures, 2011, 44, 690-695. | 2.7 | 5 |
| 138 | Scanning tunneling microscopy with InAs nanowire tips. Applied Physics Letters, 2012, 101, . | 3.3 | 5 |
| 139 | Monitoring structural influences on quantum transport in InAs nanowires. Applied Physics Letters, 2012, 101, 062104. | 3.3 | 5 |
| 140 | Direct observation of standing electron waves in diffusively conducting inas nanowire. JETP Letters, 2012, 96, 109-112. | 1.4 | 5 |
| 141 | Morphology evolution and optical properties of GaN nanoâ€pyramids grown by selective area MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 624-627. | 0.8 | 5 |
| 142 | From conformal overgrowth to lateral growth of indium arsenide nano structures on silicon substrates by MOVPE. Journal of Crystal Growth, 2013, 370, 141-145. | 1.5 | 5 |
| 143 | Hexagonal GdScO<sub>3</sub>: an epitaxial high-Îº dielectric for GaN. Semiconductor Science and Technology, 2014, 29, 075005. | 2.0 | 5 |
| 144 | 0.2 Î¼m T-gate InP/InGaAs/InP pHEMT with an InGaP diffusion barrier layer grown by LP-MOCVD using an N/sub 2/-carrier. , 0, , . | | 4 |

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| 145 | Dispersion relation, electron and hole effective masses in InxGa1âˆ'xAs single quantum wells. Journal of Applied Physics, 1996, 79, 1481-1485. | 2.5 | 4 |
| 146 | Optical and transport studies of hot electrons in modulation-doped quantum wires. Physica B: Condensed Matter, 1999, 272, 101-106. | 2.7 | 4 |
| 147 | Preparation of transparent Nb/two-dimensional electron gas contacts by using electron cyclotron resonance plasma cleaning. Journal of Applied Physics, 2000, 88, 4440. | 2.5 | 4 |
| 148 | Observation of growth during the MOVPE of III-nitrides. European Physical Journal Special Topics, 2006, 132, 177-183. | 0.2 | 4 |
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